2SC5931

Silicon NPN triple diffusion mesa type

Horizontal deflection output for TV, CRT monitor

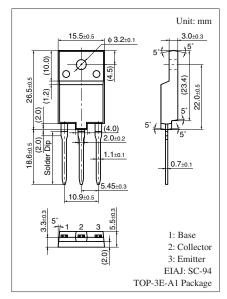
■ Features

- \bullet High breakdown voltage: $V_{CBO} \ge 1700 \text{ V}$
- High speed switching: $t_f < 200 \text{ ns}$
- Wide safe operation area

■ Absolute Maximum Ratings $T_C = 25$ °C

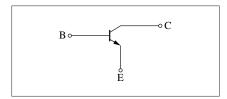
| Parameter | Symbol | Rating | Unit | |
|------------------------------------|----------------------|-------------|------|--|
| Collector-base voltage (Emitter op | en) V _{CBO} | 1700 | V | |
| Collector-emitter voltage (E-B sho | rt) V _{CES} | 1700 | V | |
| Collector-emitter voltage (Base op | en) V _{CEO} | 600 | V | |
| Emitter-base voltage (Collector op | en) V _{EBO} | 7 | V | |
| Base current | I_B | 7.5 | A | |
| Collector current | I_C | 15 | A | |
| Peak collector current * | I_{CP} | 25 | A | |
| Collector power dissipation | P _C | 60 | W | |
| $T_a = 25$ | °C | 3 | | |
| Junction temperature | T_{j} | 150 | °C | |
| Storage temperature | T _{stg} | -55 to +150 | °C | |

Note) *: Non-repetitive peak collector current



Marking Symbol: C5931

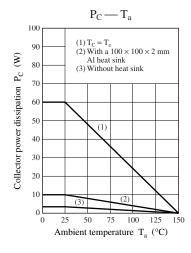
Internal Connection

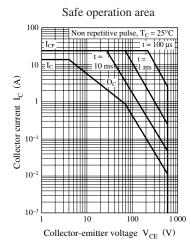


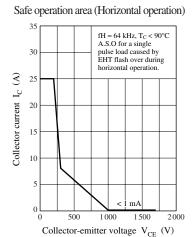
■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|---|-----|-----|-----|------|
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 1000 \text{ V}, I_{E} = 0$ | | | 50 | μΑ |
| | | $V_{CB} = 1700 \text{ V}, I_E = 0$ | | | 1 | mA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 7 \text{ V}, I_{C} = 0$ | | | 50 | μΑ |
| Forward current transfer ratio | h _{FE} | $V_{CE} = 5 \text{ V}, I_{C} = 7.5 \text{ A}$ | 5 | | 10 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 7.5 \text{ A}, I_B = 1.88 \text{ A}$ | | | 3 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | $I_C = 7.5 \text{ A}, I_B = 1.88 \text{ A}$ | | | 1.5 | V |
| Transition frequency | f_T | $V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 0.5 \text{ MHz}$ | | 3 | | MHz |
| Storage time | t _{stg} | $I_C = 7.5$ A, Resistance loaded | | | 2.7 | μs |
| Fall time | t _f | $I_{B1} = 1.88 \text{ A}, I_{B2} = -3.75 \text{ A}$ | | | 0.2 | μs |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.







2 SJD00314AED

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